SOT89 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

BF621

ISSUE 3 – MARCH 2001 ✪

FEATURES

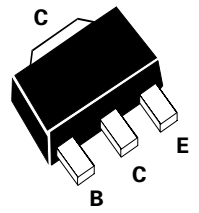
* High breakdown and low saturation voltage

APPLICATIONS

* Suitable for video output stages in TV sets
* Switching power supplies

COMPLEMENTARY TYPE – BF620

PARTMARKING DETAIL – DF



SOT89

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-100	mA
Continuous Collector Current	I_C	-50	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	-1	W
Operating and Storage Temperature Range	T_j:T_{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300		V	I_C=-10μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300		V	I_C=-1mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	I_E=-100μA, I_C=0
Collector Cut-Off Current	I_{CBO}		-10 -20	nA μA	V_{CB}=-200V, I_E=0 V_{CB}=-200V, I_E=0 †
Colector Cut-Off Current	I_{CER}		-50 -10	nA μA	V_{CE}=-200V, R_{BE}=2.7KΩ V_{CE}=-200V, R_{BE}=2.7KΩ †
Emitter Cut-Off Current	I_{EBO}		-10	μA	V_{EB}=-5V, I_C=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.6	V	I_C=-30mA, I_B=-5mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	V	I_C=-20mA, I_B=-2mA*
Static Forward Current Transfer Ratio	h_{FE}	50			I_C=-25mA, V_{CE}=-20V*
Transition Frequency	f_T	100 Typical		MHz	I_C=-10mA, V_{CE}=-10V f=100MHz
Output Capacitance	C_{obo}	0.8 Typical		pF	V_{CB}=-30V, f=1MHz

†T_{amb}=150°C
*Measured under pulsed conditions.
For typical characteristics graphs see FMMTA92 datasheet.

ZETEX